

# Generating *All* 2-Transistor Circuits Leads to New Wide-Band CMOS LNAs

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## Aim

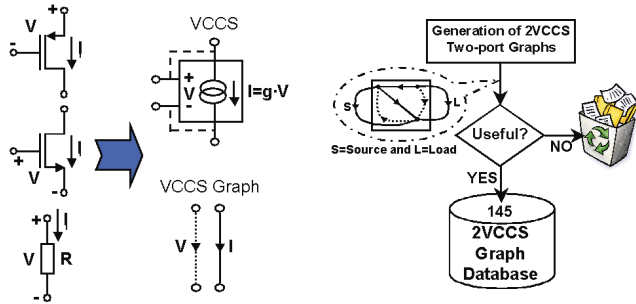
- Find *new* 2-Transistor wide band CMOS Low-Noise Amplifier (LNA) circuits.

## Motivations

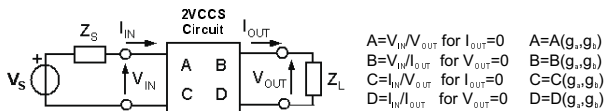
- Wide band LNAs are widely used in communication/instrumentation.
- Few different wide band LNAs alternatives in literature.
- Known LNAs are often simple circuits, which can be seen as 2-Transistor circuits or a combination of them.

## Our Approach: Systematic Generation

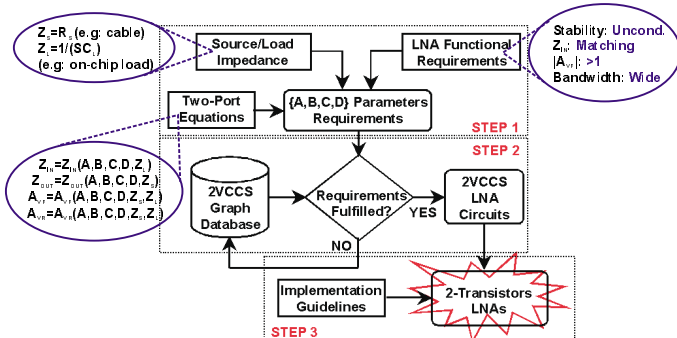
- Systematic** generation of **ALL** possible 2-Transistor circuits via graph based generation of **ALL** Two-ports with 2 VCCSs.



- 2VCCS Two-ports are characterized in terms of the *values and combinations* of  $\{A, B, C, D\}$  parameters, which depend on  $g_1$  and  $g_2$  (the transconductances of the 2 VCCSs), resulting in **145 potentially useful graphs** (the 2VCCS database) with at least **one non-zero** transmission parameter.



- Generation of ALL 2-Transistor Wide Band LNAs:** within the 2VCCS database we find **ALL** the circuits that do behave as *wide band LNAs* using the following 3-steps methodology:



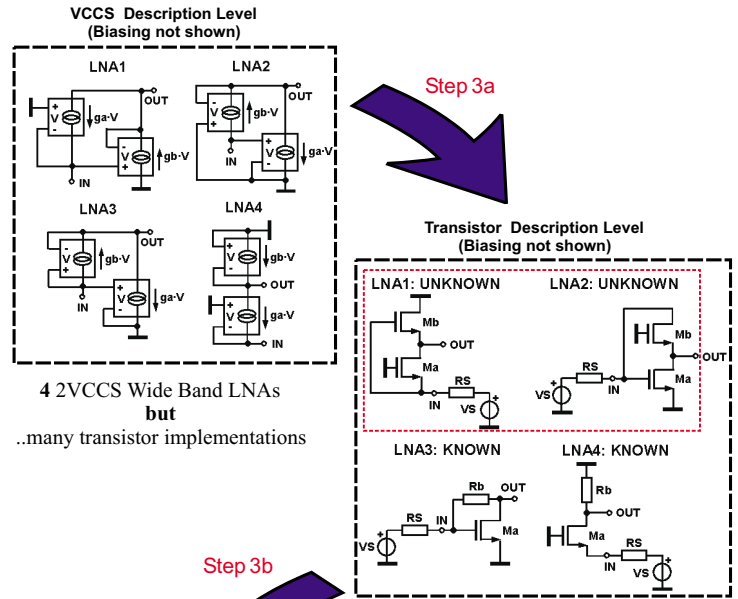
**Step 1:** LNA *small signal* functional requirements are translated into constraints for the  $\{A, B, C, D\}$  parameters upon proper source  $Z_S$  and load  $Z_L$  impedance (see the flow-chart).

**Step 2:** The 2VCCS graph database is explored for cases meeting the above requirements: **these are 2VCCS Wide Band LNAs**.

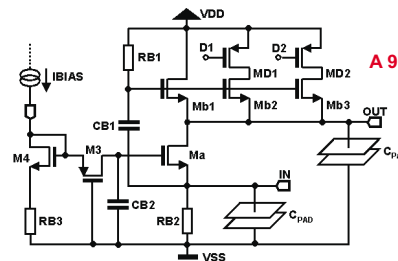
**Step 3:** MOS transistor implementation:

- ➔ a) **VCCS:** single NMOS (faster than PMOS) or Resistor (if possible).
- ➔ b) **Circuit arrangement:** *bias current re-use* is exploited to minimize DC power OR performance degradation due to biasing circuitry.

## The Output of the Generation



**2 Known: LNA3 and LNA4**  
**2 Unknown: LNA1 and LNA2!**



**A 900MHz Wide Band CMOS LNA Design Based on the LNA1**

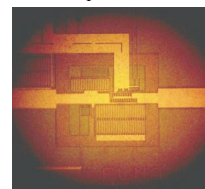
- Two-stages in Feed-forward: Mb1,2,3 *CS-stage* and Ma-Mb1,2,3 *CG-stage*.
- Input signal "ac" coupled to Mb1,2,3 via the CB1-RB1 high-pass filter.
- Variable Gain: from 6 to 12dB in 4 discrete steps.
- Switches out of the signal path ----> minimum performance degradation.

## Measurements

$A_{VF}$	11 dB
-3dB Bandwidth	900MHz
VSWR <sub>in</sub>	<1.6
$A_{IP}$	< -30dB
IIP2	15dBm
IIP3	1dBm
NF	< 4.5dB
Supply Voltage	3.3V
Supply Current	1.5mA
Technology	0.35μm CMOS
Die Area	0.06mm <sup>2</sup>

Measurements at Max Gain:  $R_S=75\Omega$  and  $C_L=0.2pF$ .

Chip Photo



## Conclusions

- ➔ A methodology generating **ALL** 2-Transistors wide band LNAs has been presented, yielding to **2 new** circuits.
- ➔ An LNA prototype realized using an industrial 0.35μm CMOS process shows 900MHz bandwidth draining only 1.5mA, good linearity and NF<4.5dB (e.g.: suitable for cable modem or cable TV applications).
- ➔ This systematic generation approach can be used to select other class of linear circuits.

## Acknowledgments

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